

FORM PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. FIS920030183US1	Application No. 10/605,108
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)		Applicant Dureseti CHIDAMBARRAO, et al.	
		Filing Date 09/09/2003	Group 2814

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EXAMINER <span style="font-family: cursive; font-size: 1.2em;">Long Pham</span>	DATE CONSIDERED <span style="font-family: cursive; font-size: 1.2em;">6/5/06</span>
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\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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